

DOCKET NO. SC12858TP

Please amend the subject application as follows:

IN THE SPECIFICATION:

On page 1, lines 1 and 2, amend the title as follows:

METHOD FOR FORMING A NON-VOLATILE MEMORY HAVING A REFERENCE
TRANSISTOR AND METHOD FOR FORMING

On page 1, lines 5-10, amend the related application paragraph as follows:

RELATED APPLICATION

This application is related to United States patent application ~~attorney docket number~~
~~SC12996TC~~ Serial No. 10/609,359, entitled "Variable Gate Bias For A Reference Transistor In
A Non-Volatile Memory" filed concurrently herewith by Chindalore et al., and assigned to the
assignee hereof.

On page 2, lines 1 and 2, amend the title as follows:

METHOD FOR FORMING A NON-VOLATILE MEMORY HAVING A REFERENCE
TRANSISTOR AND METHOD FOR FORMING